

CD4094B Types

DATA

CLOCK

STROBE

DATA

CLOCK-

Q I

Q2

03.

04

¥ss

8-STAGE

REGISTER

8-611

REGISTE

IJ

3-STATE OUTPUTS

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(TERMINALS 4, 5, 6, 7, 14, 13, 12, 11, RESPECTIVELY) 9205 - 24564Ri

FUNCTIONAL DIAGRAM

-OUTPUT ENABLE

9205 25642

16 VDD

15

14 - 95

13 - 96

12 - 07

10

TOP VIEW

- 08

- º's

Qs

PARALLEL OUTPUTS Q

CMOS 8-Stage Shift-and-Store **Bus Register**

High-Voltage Types (20-Volt Rating)

CD4094B is an 8-stage serial shift register having a storage latch associated with each stage for strobing data from the serial input to parallel buffered 3-state outputs. The parallel outputs may be connected directly to common bus lines. Data is shifted on positive clock transitions. The data in each shift register stage is transferred to the storage register when the STROBE input is high. Data in the storage register appears at the outputs whenever the OUTPUT-ENABLE signal is high.

Two serial outputs are available for cascading a number of CD4094B devices. Data is available at the OS serial output terminal on positive clock edges to allow for high-speed operation in cascaded systems in which the clock rise time is fast. The same serial information, available at the Ω_{S}^{\prime} terminal on the next negative clock edge, provides a means for cascading CD4094B devices when the clock rise time is slow.

The CD4094B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic package (E suffix), and in chip form (H suffix).

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Features:

- 3-state parallel outputs for connection to common bus Separate serial outputs synchronous to both positive
- and negative clock edges for cascading Medium speed operation -- 5 MHz at 10 V (typ.)
- Standardized, symmetrical output characteristics
- 100% tested for guiescent current at 20 V
- Maximum input current of 1 µA at 18 V over full package temperature range; 100 nA at 18 V and 25°C
- Noise margin (full package temperature range): $1 \text{ V at V}_{DD} = 5 \text{ V}$ 2 V at V_{DD} = 10 V 2.5 V at V_{DD} = 15 V
- = 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices'

Applications:

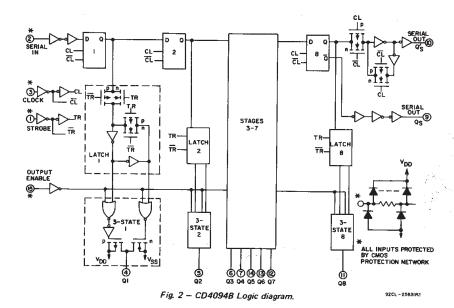
- Serial-to-parallel data conversion
- Remote control holding register



MAXIMUM RATINGS, Absolute-Maximum Values: DC SUPPLY-VOLTAGE RANGE, (VDD)

| Voltages referenced to VSS Terminal) | |
|--|---|
| INPUT VOLTAGE RANGE, ALL INPUTS | -0.5V to Vpp +0.5V |
| DC INPUT CURRENT, ANY ONE INPUT | ±10mA |
| POWER DISSIPATION PER PACKAGE (PD): | |
| For $T_A = -55^{\circ}C$ to $+100^{\circ}C$ | |
| For T _A = +100°C to +125°CDerat DEVICE DISSIPATION PER OUTPUT TRANSISTOR | te Linearity at 12mW/ ^o C to 200mW |
| FOR T _A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) | 100mW |
| OPERATING-TEMPERATURE RANGE (TA) | |
| STORAGE TEMPERATURE RANGE (Tstg) | -65°C to +150°C |
| LEAD TEMPERATURE (DURING SOLDERING): | |
| | |

At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max+265°C



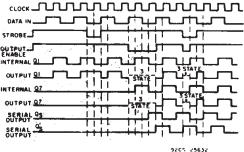


Fig. 3 – Timing diagram.

RECOMMENDED OPERATING CONDITIONS at $T_A = 25^{\circ}C$, Except as Noted. For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

| CHARACTERISTIC | VDD (V) | Lif | | |
|---|------------|------|--------|-------|
| | | MIN. | MAX. | UNITS |
| Supply-Voltage Range (For TA=Full Package-Temperature Range) | | 3 | 18 | V |
| Data Setup Time, ts | 5 | 125 | _ | |
| | 10 | 55 | — · | ns |
| | 15 | 35 | - | 1 |
| | 5 | 200 | | |
| Clock Pulse Width, tw | 10 | 100 | - | ns |
| | 15 | 83 | | |
| | 5 | | 1.25 | |
| Clock Input Frequency, fcL | 10 | dc | 2.5 | MHz |
| | 15 | | 3 | |
| Clock Input Rise or Fall time, | 5 | 1 | 15 | |
| t _r CL, t _f CL:* | 10 15 | - | 5 5 | μs |
| | 5 | 200 | - | 1 |
| Strobe Pulse Width, tw | 10 | 80 | - | ns |
| | 15 | 70 | - 1 | |

*If more than one unit is cascaded trCL (for Os only) should be made less than or equal to the sum of the fixed propagation delay at 50 pF and the transition time of the output driving stage for the estimated capacitive load.

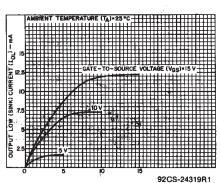
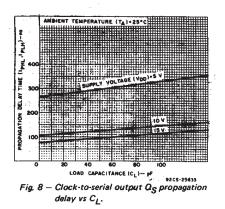


Fig. 5 – Minimum output low (sink) current characteristics.



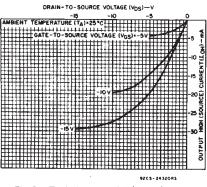
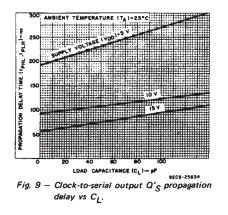
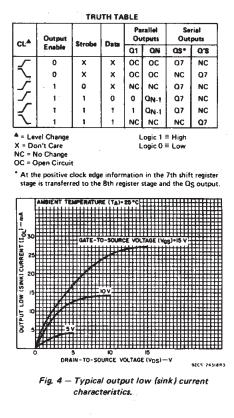


Fig. 6 – Typical output high (source) current characteristics.





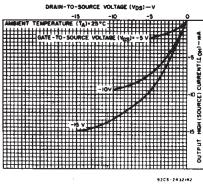
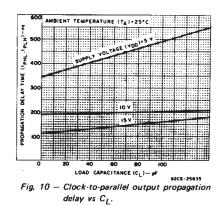


Fig. 7 — Minimum output high (source) current characteristics.

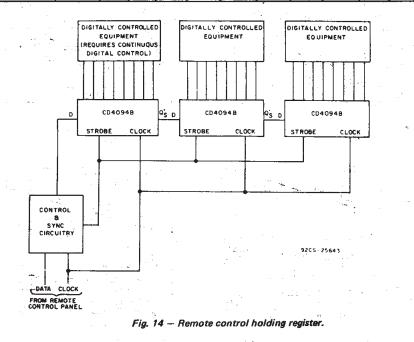


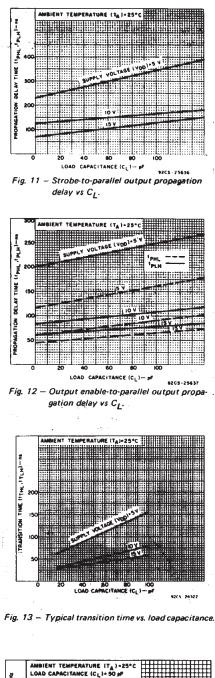
COMMERCIAL CMOS HIGH VOLTAGE ICs

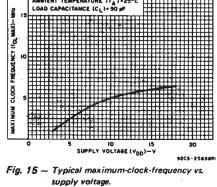
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STATIC ELECTRICAL CHARACTERISTICS

| CHARACTER- ISTIC | CONDITIONS | | | LIMITS AT INDICATED TEMPERATURES (°C) | | | | | | LINUTE | | |
|---|------------|------|-----|---------------------------------------|-------|-------|-------|-------|------------------|----------|------------------|--|
| | Vo | VIN | VDD | · · [| | | | +25 | | | UNITS | |
| | (V) | (V) | (v) | -55 | 40 | +85 | +125 | Min. | Тур. | Max. | | |
| Quiescent Device | - | 0,5 | 5 | 5 | 5 | 150 | 150 | - | 0.04 | 5 | | |
| Current, | - | 0,10 | 10 | 10 | 10 | 300 | 300 | - | 0.04 | -10 | μA | |
| IDD Max. | | 0,15 | 15 | 20 | 20 | 600 | 600 | - | 0.04 | 20 | μ <i>μ</i> Α | |
| | - | 0,20 | 20 | 100 | 100 | 3000 | 3000 | - ' | 0.08 | 100 | 1 | |
| Output Low | 0.4 | 0,5 | 5 | 0.64 | 0.61 | 0.42 | 0.36 | 0.51 | 1 | - | | |
| (Sink) Current IOL Min. | 0.5 | 0,10 | 10 | 1.6 | 1.5 | 1.1 | 0.9 | 1.3 | 2.6 | - | | |
| | 1.5 | 0,15 | 15 | 4.2 | 4 | 2.8 | 2.4 | 34 | 6.8 | 12 | | |
| Output High | 4.6 | 0,5 | 5 | -0.64 | -0.61 | -0.42 | -0.36 | -0.51 | -1 | - | mA | |
| Output High (Source) Cyrrent, TOH Min. | 2.5 | 0,5 | 5 | -2 | -1.8 | -1.3 | -1.15 | -1.6 | - 3.2 | | | |
| | 9,5 | 0,10 | 1.0 | -1.6 | -1.5 | -1.1 | -0.9 | -1.3 | -2.6 | | | |
| TOH WITT | 13.5 | 0,15 | 15 | -4.2 | -4 | -2.8 | -2.4 | -3.4 | -6.8 | | - | |
| Output Voltage: Low-Level, | | 0,5 | 5 | 1 B | 0 | .05 | | _ | 0 | 0.05 | | |
| | San (1 | 0,10 | 10 | 1 - 1 | 0 | .05 | | | 0 | 0.05 | , | |
| VOL Max. | | 0,15 | 15 | 0.05 | | | - : | 0 | 0.05 | v | | |
| Output Voltage: | - | 0,5 | 5 | | 4 | .95 | | 4.95 | 5 | - | v | |
| • | - | 0,10 | 10 | 9.95 9.95 10 - | | | | - | | | | |
| VOH Min. | - | 0,15 | 15 | 14.95 | | | | 14.95 | 15 | - | | |
| Input Low | 0.5, 4.5 | | 5 | 1.5 1.5 | | | | | 1.5 | | | |
| Input Low Voltage, | 1, 9 | - | 10 | 3 | | | | | 3 | | | |
| | 1.5,13.5 | - | 15 | 4 | | | | | - | 4 | | |
| Current, IDD Max. Output Low (Sink) Current IOL Min. Output High (Source) Current, IOH Min. Output Voltage: Low-Level, VOL Max. Output Voltage: High-Level, VOH Min. Input Low Voltage, VIL Max. Input High Voltage, | 0.5, 4.5 | | 5 | | | 3.5 | | 3.5 | - | _ | V | |
| | 1, 9 | - | 10 | | | 7 | | .7 | - | <u> </u> | | |
| VIH Min. | 1.5,13.5 | - | 15 | 11 | | | | 11 | - | — | н. н. Пология | |
| | - | 0,18 | 18 | ±0.1 | ±0.1 | ±1 | ±1 | - | ±10-5 | ±0.1 | μA | |
| Leakage Current | 0,18 | 0,18 | 18 | ±0.4 | ±0.4 | ±12 | ±12 | | ±10 ⁴ | ±0.4 | μA | |







DYNAMIC ELECTRICAL CHARACTERISTICS

At $T_A=25^{\circ}C$; Input t_r , $t_f = 20 \text{ ns}$, $C_L = 50 \text{ pF}$, $R_L = 200 \text{ k}\Omega$

| CHARACTERISTIC | VDD | | UNITS | | |
|--|---------|---------|-------|---------|-----|
| | (V) | MIN. | TYP. | MAX. | |
| Propagation Delay Time, | | | | | |
| tPHL, tPLH | 5 | | 300 | 600 | |
| Clock to Serial Output QS | 10 | | 125 | 250 | ns |
| Clock to Serial Output US | 15 | | 95 | 190 ··· | 115 |
| · · · · · · · · · · · · · · · · · · · | 5 | _ | 230 | 460 | |
| Clock to Serial Output O'S | 10 | - 1 | 110 | 220 | ns |
| 5 | 15 | - | 75 | 150 | |
| | 5 | - | 420 | 840 | |
| Clock to Parallel Output | 10 | - | 195 | 390 | ns |
| · · · · · · · · · · · · · · · · · · · | 15 | - | 135 | 270 | |
| | - 5 | - | 290 | 580 | |
| Strobe to Parallel Output | 10 | - | 145 | 290 | ns |
| · · · · · · · · · · · · · · · · · · · | 15 | | 100 | 200 | |
| Output Enable to Parallel | 5 | - | 140 | 280 | |
| Output: | 10 | - | 60 | 120 | ns |
| ^t PHZ ^{, t} PZH | 15 | - | 45 | 90 | |
| | 5 | - | 100 | 200 | |
| tPLZ, tPZL | 10 | - | 50 | 100 | ns |
| · | 15 | - | 40 | 80 | |
| Minimum Strobe Pulse | 5 | - | 100 | 200 | |
| Width, tw | 10 | | _ 40 | 80 | ns |
| | 15 | - | 35 | 70 | |
| Minimum Clock Pulse | 5 | - | 100 | 200 | |
| Width, tw | 10 | - | 50 | 100 | ns |
| | 15 | - | 40 | 83 | |
| Minimum Data Setup | 5 | - | 60 | 125 | |
| Time, t _S | 10 | - | 30 | 55 | ns |
| | 15 | - | 20 | 35 | |
| Transition Time; | 5 | - | 100 | 200 | |
| THL, TLH | 10 | — · | 50 | 100 | ins |
| | 15 | - | 40 | 80 | |
| Maximum Clock Input Rise | 5 10 | 15 5 | | _ | |
| or Fall Time, t _r CL, t _f CL | 15 | 5 | | _ | μs |
| Maximum Clock Input | 5 | 1.25 | 2.5 | | |
| Frequency, fCL | 10 | 2.5 | 5 | | MH: |
| · . | 15 | 3 | 6 | - | |
| Input Capacitance CIN | _ | | 5 | 7.5 | pF |
| (Any Input) | | | | 1.0 | h. |

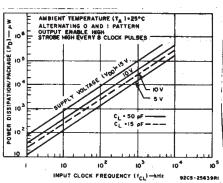


Fig. 16 – Dynamic power dissipation vs input clock frequency.

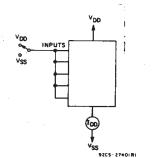
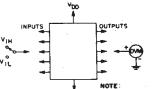


Fig. 17 – Quiescent device current test circuit.



VSS TEST ANY COMBINATION OF INPUTS 9205-2744 IAI

Fig. 18 - Input voltage test circuit.

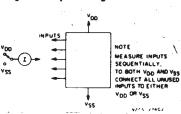
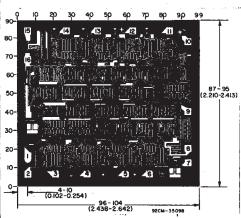


Fig. 19 – Input current test circuit.



Dimensions and Pad Layout for CD4094B Chip.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch) .

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